

ABSTRACT OF THE DISCLOSURE

An integrated circuit for electrostatic discharge (ESD) protection that comprises a silicon-controlled rectifier (SCR), a first transistor of a first type integrally formed with the SCR including a first gate, a second transistor of a second type integrally formed with the SCR including a second gate, and a control circuit in response to a first voltage applied to the first and second gates providing a first holding voltage to the SCR to keep the SCR from latching-up, and in response to a second voltage applied to the first and second gates providing a second holding voltage to the SCR to keep the SCR in the latch-up state.